

Attorney's Docket No.:07977-258001

In the claims:

1. (Previously amended) A method of manufacturing a semiconductor device, wherein a material having a tensile stress of 8×10^9 dynes/cm² or more is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

2. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said material is formed by LPCVD within a temperature range of between 500 and 900°C.

3. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said material is formed by LPCVD within a pressure range of between 0.1 and 3 Torr.

4. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said material is formed by LPCVD with a gas containing chlorine as a material gas.

5 - 6 (withdrawn)

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7. (Previously amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a temperature range of between 500 and 900°C is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

8. (Previously amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a pressure range of between 0.1 and 3 Torr is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

9. (Previously amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD with a gas containing chlorine as a material gas is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

10 - 19 (Withdrawn)

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Sub C7

20. (Amended) A method of manufacturing a semiconductor device according to claim 4 or 9, wherein the gas containing chlorine is a mixture gas that contains any one of SiCl_4 , SiH_2Cl_2 , SiCl_3 , and Si_2Cl_6 .

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21 - 59 (Withdrawn)

Please add new claims 60 to 66 as follows:

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60. (New) A method of manufacturing a semiconductor device according to claim 9, wherein the gas containing chlorine is a mixture gas that contains any one of SiCl_4 , SiH_2Cl_2 , SiCl_3 , and Si_2Cl_6 .

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61. (New) A method of manufacturing a semiconductor device comprising the steps of:

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forming a semiconductor film over a substrate;
forming a material having a tensile stress of 8×10^9 dynes/cm² or more in contact with the semiconductor film to getter an impurity element in the semiconductor film therein;
removing the material having a tensile stress of 8×10^9 dynes/cm² or more from the semiconductor film;
forming a gate insulating film over the semiconductor film;
forming a gate electrode over the gate insulating film.

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62. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is formed by LPCVD within a temperature range of between 500 and 900°C.

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63. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is formed by LPCVD within a pressure range of between 0.1 and 3 Torr.

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64. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is formed by LPCVD with a gas containing chlorine as a material gas.

65. (New) A method of manufacturing a semiconductor device according to claim 60, wherein said material is a silicon nitride film formed by LPCVD.

66. (New) A method of manufacturing a semiconductor device according to claim 64, wherein a composition ratio of N/Si in said silicon nitride film is between 1.2 and 1.4.